

	Hits	Search Text	DBs
1	0	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and (polymer\$6 same (acid\$3 near3 sensitiv\$4) same ((acid near3 (generat\$4 or liberat\$4)) or PAG) same acid\$3labil\$3 same acid\$3cataly\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or ion near3 implant\$4 or dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	0	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same (acid\$3 near3 sensitiv\$4) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4))) same acid\$3labil\$3 same acid\$3cataly\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or ion near3 implant\$4 or dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	0	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same (acid\$3 near3 sensitiv\$4) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4))) same acid\$3labil\$3 same acid\$3cataly\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4) or dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	20	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4))) same acid\$3labil\$3 same acid\$3cataly\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4) or dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	49	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4)))) and acid\$3labil\$3 and acid\$3cataly\$4 and (acid near4 sensitiv\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	14	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4)))) and (acid\$3labil\$3 same (ketal or acetal or ortho\$2ester)) and acid\$3cataly\$4 and (acid near4 sensitiv\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4)) and (heat\$4 or bak\$3 or post\$3bak\$4 or thermal\$4treat\$4 or thermal\$3process\$4) and (water or humidity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	14	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4)))) and (acid\$3labil\$3 same (ketal or acetal or ortho\$2ester)) and acid\$3cataly\$4 and (acid near4 sensitiv\$4) and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or RIE or (ion near3 implant\$4)) and (heat\$4 or bak\$3 or post\$3bak\$4 or thermal\$4treat\$4 or thermal\$3process\$4) and ((water or humidity or moisture) same (treat\$4 or react\$4 or mix\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	24	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4)))) and acid\$3labil\$3 and acid\$3cataly\$4 and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4) or RIE) and ((heat\$3 or bak\$3 or thermal\$3treat\$4 or (thermal\$3 near3 process\$4)) same (humid\$3 or water or moisture) same (temperature or "\$3C"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	30	((substrate or wafer) same (pattern\$4 or structure) same (resist or photoresist)) and ((polymer\$6 or photoresist or resist) same ((acid near3 (generat\$4 or liberat\$4)) or PAG or (photo\$1acid near3 (generat\$4 or liberat\$4)))) and acid\$3labil\$3 and acid\$3cataly\$4 and (expos\$4 or illuminat\$4 or irradiat\$4) and develop\$4 and (etch\$4 or (ion near3 implant\$4) or RIE) and ((heat\$3 or bak\$3 or thermal\$3treat\$4 or (thermal\$3 near3 process\$4)) same (humid\$3 or water or moisture) same (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB